

AMENDMENTS TO THE CLAIMS:

1-11. (cancelled)

12. (previously amended) An improved p-type gallium nitride-based semiconductor device comprising:

a device structure that includes at least one p-type Group III nitride layer that includes some gallium;

a plurality of silicon dioxide portions on said p-type Group III nitride layer;

a portion of a Group II metal source composition layer on each of said silicon dioxide portions; and

a second silicon dioxide layer on said Group II metal source composition layer,

wherein said second silicon dioxide layer is limited to said source composition layer portions.

13-47. (cancelled)

48. (currently amended) ~~A semiconductor device according to Claim 47, comprising:~~
An improved p-type gallium nitride-based semiconductor device comprising:

a conductive silicon carbide substrate;

a conductive buffer layer on said silicon carbide substrate for providing a crystal transition between said substrate and Group III nitride portions of said device;

an n-type Group III nitride layer on said buffer layer;

a p-type Group III nitride layer that includes some gallium directly on said n-type layer and forms a p-n junction;

a plurality of silicon dioxide portions on said p-type Group III nitride layer;

a portion of ~~said~~ a magnesium source composition layer on each of said silicon dioxide portions; and

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a second silicon dioxide layer on said magnesium source composition layer,
wherein said second silicon dioxide layer is limited to said magnesium source
composition layer portions.

49. (cancelled)